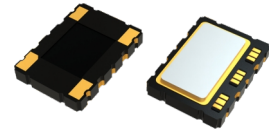


7.0 x 5.0 mm SMD Voltage Controlled Temperature Compensated Crystal Oscillator

Feature

- Typical 7.0 x 5.0 x 1.9 mm ceramic package
- Compactness and light weight
- Low power consumption
- VCTCXO available



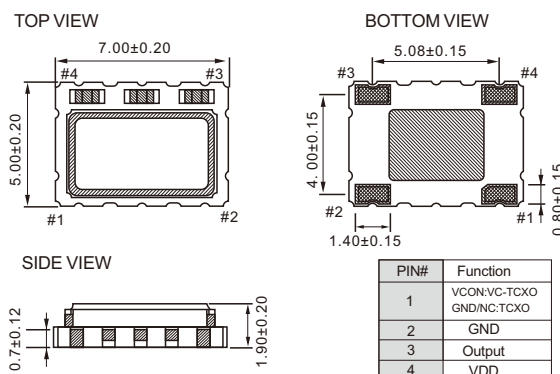
Electrical Specifications

Parameter		3.3/3.0		2.5V		Unit
		Min.	Max.	Min.	Max.	
Supply Voltage Variation		V _{DD} -5%	V _{DD} +5%	V _{DD} -5%	V _{DD} +5%	V
Frequency Range		5	52	5	52	MHz
Standard Frequency		5,6.4,8,8.192,10,12.5,12.8,16,16.384,19.44,25,26				MHz
Frequency Tolerance*		-	±2.0	-	±2.0	ppm
Frequency stability	VS Supply V(±5%) change	-	±0.1	-	±0.1	ppm
	VS Load(±10%) change	-	±0.2	-	±0.2	
	VS Aging(@1 st year)	-	±1.0	-	±1.0	
Supply Current(Clipped Sine)		-	3.5	-	3.5	mA
Supply Current(CMOS)		-	6	-	6	mA
Clipped sine wave	Output Level	0.8	-	0.8	-	V _{p-p}
	Load	10kΩ//10pF		10kΩ//10pF		
CMOS	Output High	0.9V _{DD}	-	0.9V _{DD}	-	V
	Output Low	-	0.1V _{DD}	-	0.1V _{DD}	V
	Load	15		15		pF
	Duty	45	55	45	55	%
Control Voltage Range(VCTCXO)		0.5	2.5	0.4	2.4	V
Pulling Range (VCTCXO)		±5	±12	±5	±12	ppm
Vc Input Impedance(VCTCXO)		100	-	100	-	kΩ
Phase Noise	100Hz	-115		-115		dBc/Hz
@19.2MHz	1KHz	-135		-135		
Clipped Sine	10KHz	-148		-148		
Start Time		-	2	-	2	mSec
Storage Temp. Range		-55	125	-55	125	°C

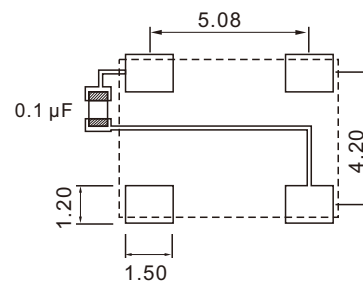
Standard frequencies are frequencies which the crystal has been designed and does not imply a stock position

* Frequency at 25°C, 1 hour after reflow.

Dimension(mm)



Solder Pad Layout(mm)



To ensure optimal oscillator performance, place a by-pass capacitor of 0.1 μF as close to the part as possible between Vdd and GND pads.

FREQ. STABILITY vs. TEMP. RANGE

Temp. (°C)	ppm	±0.5	±1.0
-20 ~ +70		○	○
-30 ~ +85		○	○
-40 ~ +85		○	○

○: Available △ :Conditional X: Not available